

Complementary Silicon High-Power Transistors

... for general-purpose power amplifier and switching applications.

- 10 A Collector Current
- Low Leakage Current —
 $I_{CEO} = 0.7 \text{ mA @ } 60 \text{ V}$
- Excellent dc Gain —
 $h_{FE} = 40 \text{ Typ @ } 3.0 \text{ A}$
- High Current Gain Bandwidth Product —
 $h_{fe} = 3.0 \text{ min @ } I_C = 0.5 \text{ A,}$
 $f = 1.0 \text{ MHz}$

MAXIMUM RATINGS

Rating	Symbol	TIP33C TIP34C	Unit
Collector–Emitter Voltage	V_{CEO}	100 V	Vdc
Collector–Base Voltage	V_{CB}	100 V	Vdc
Emitter–Base Voltage	V_{EB}	5.0	Vdc
Collector Current — Continuous Peak (1)	I_C	10 15	Adc
Base Current — Continuous	I_B	3.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	80 0.64	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +150	$^\circ\text{C}$

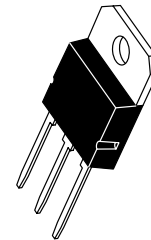
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.56	$^\circ\text{C/W}$
Junction–To–Free–Air Thermal Resistance	$R_{\theta JA}$	35.7	$^\circ\text{C/W}$

(1) Pulse Test: Pulse Width = 10 ms, Duty Cycle \leq 10%.

**NPN
TIP33C
PNP
TIP34C**

**10 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
100 VOLTS
80 WATTS**



**CASE 340D–02
TO–218AC**

TIP33C TIP34C

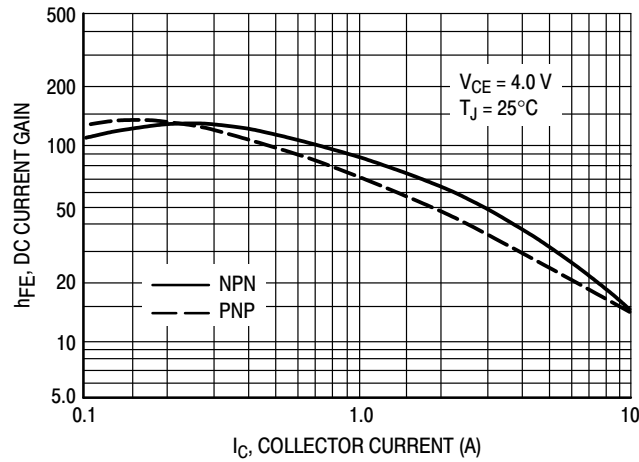


Figure 1. DC Current Gain

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (1) ($I_C = 30$ mA, $I_B = 0$)	$V_{CEO(sus)}$	100	—	Vdc
Collector–Emitter Cutoff Current ($V_{CE} = 60$ V, $I_B = 0$)	I_{CEO}	—	0.7	mA
Collector–Emitter Cutoff Current ($V_{CE} = \text{Rated } V_{CEO}$, $V_{EB} = 0$)	I_{CES}	—	0.4	mA
Emitter–Base Cutoff Current ($V_{EB} = 5.0$ V, $I_C = 0$)	I_{EBO}	—	1.0	mA
ON CHARACTERISTICS (1)				
DC Current Gain ($I_C = 1.0$ A, $V_{CE} = 4.0$ V) ($I_C = 3.0$ A, $V_{CE} = 4.0$ V)	h_{FE}	40 20	— 100	—
Collector–Emitter Saturation Voltage ($I_C = 3.0$ A, $I_B = 0.3$ A) ($I_C = 10$ A, $I_B = 2.5$ A)	$V_{CE(sat)}$	— —	1.0 4.0	Vdc
Base–Emitter On Voltage ($I_C = 3.0$ A, $V_{CE} = 4.0$ V) ($I_C = 10$ A, $V_{CE} = 4.0$ V)	$V_{BE(on)}$	— —	1.6 3.0	Vdc
DYNAMIC CHARACTERISTICS				
Small–Signal Current Gain ($I_C = 0.5$ A, $V_{CE} = 10$ V, $f = 1.0$ kHz)	h_{fe}	20	—	—
Current–Gain — Bandwidth Product ($I_C = 0.5$ A, $V_{CE} = 10$ V, $f = 1.0$ MHz)	f_T	3.0	—	MHz

(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

TIP33C TIP34C

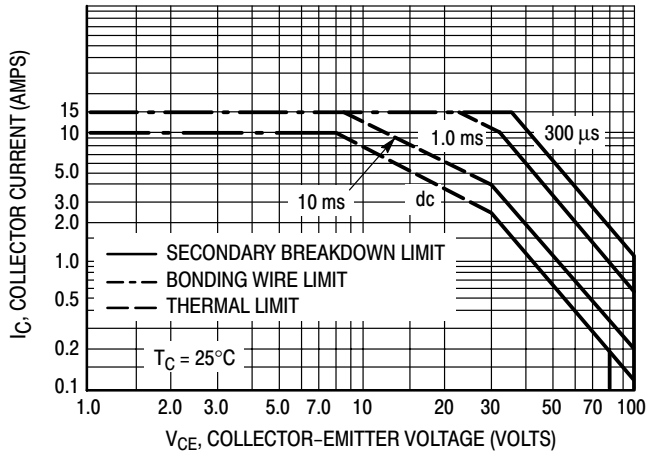


Figure 2. Maximum Rated Forward Bias Safe Operating Area

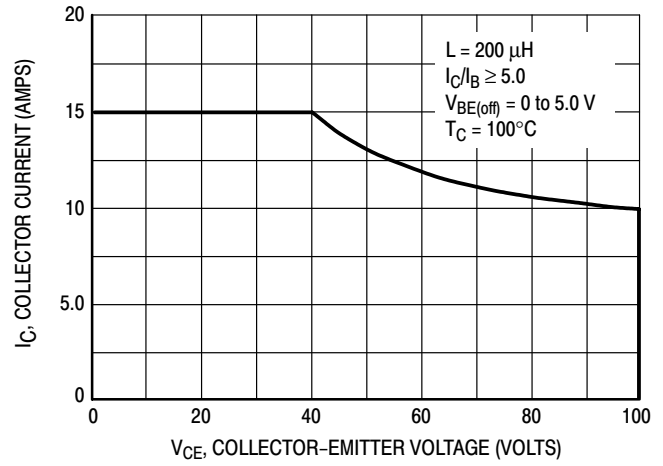


Figure 3. Maximum Rated Forward Bias Safe Operating Area

FORWARD BIAS

The Forward Bias Safe Operating Area represents the voltage and current conditions these devices can withstand during forward bias. The data is based on $T_C = 25^\circ\text{C}$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10%, and must be derated thermally for $T_C > 25^\circ\text{C}$.

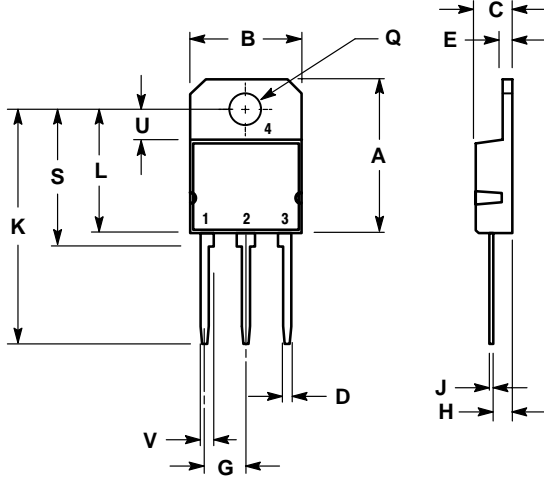
REVERSE BIAS

The Reverse Bias Safe Operating Area represents the voltage and current conditions these devices can withstand during reverse biased turn-off. This rating is verified under clamped conditions so the device is never subjected to an avalanche mode.

TIP33C TIP34C

PACKAGE DIMENSIONS


CASE 340D-02 ISSUE E



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	20.35	---	0.801
B	14.70	15.20	0.579	0.598
C	4.70	4.90	0.185	0.193
D	1.10	1.30	0.043	0.051
E	1.17	1.37	0.046	0.054
G	5.40	5.55	0.213	0.219
H	2.00	3.00	0.079	0.118
J	0.50	0.78	0.020	0.031
K	31.00	REF	1.220	REF
L	---	16.20	---	0.638
Q	4.00	4.10	0.158	0.161
S	17.80	18.20	0.701	0.717
U	4.00	REF	0.157	REF
V	1.75	REF	0.069	

- STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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